

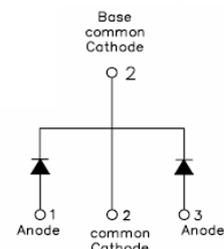
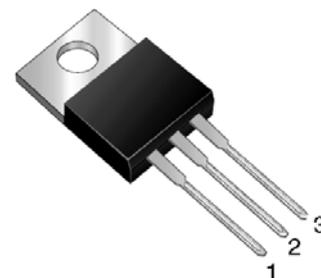
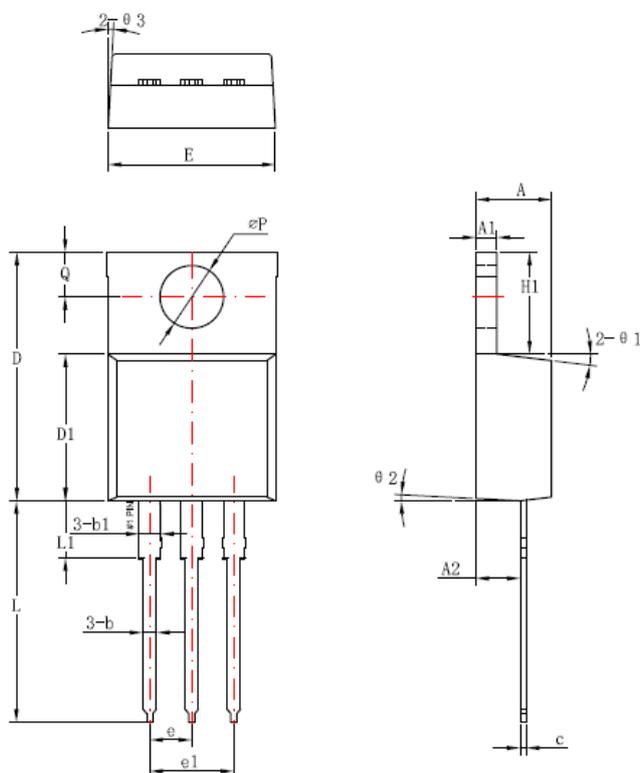
MBR2080CTL SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request


Mechanical Dimensions: In mm


Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1		5.06	
H1	6.04	6.24	6.44
L	12.7	13.56	13.78
L1		3.5	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
θ1		7°	
θ2		3°	
θ3		4°	

TO-220AB

Marking Diagram:


Where XXXXX is YYWWL

MBR	= Device Type
20	= Forward Current (20A)
80	= Reverse Voltage (80V)
CTL	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR2080CTL	TO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	80	V
Average Rectified Forward Current(per device)	I_o	50% duty cycle @ $T_c=100^{\circ}C$, rectangular wave form	20	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	150	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg) *	V_{F1}	@ 10 A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.75	V
Reverse Current (per leg) *	I_{R1}	@ $V_R = \text{rated } V_R$ $T_C = 25\text{ }^\circ\text{C}$	1.0	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_C = 125\text{ }^\circ\text{C}$	50	mA
Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	500	pF
Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	2.0	$^\circ\text{C/W}$
Approximate Weight	wt	-	2.0	g
Case Style	TO-220AB			

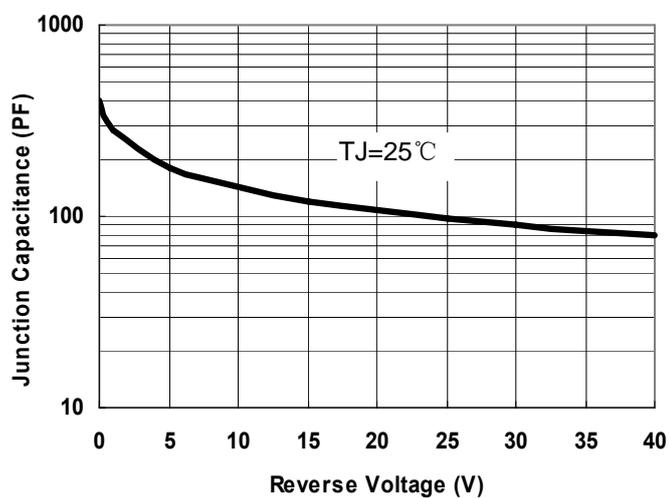


Fig.1-Typical Junction Capacitance

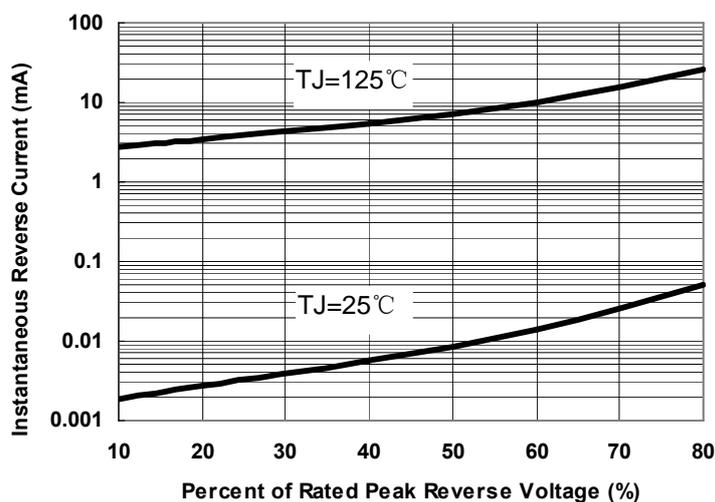


Fig.2-Typical Reverse Characteristics

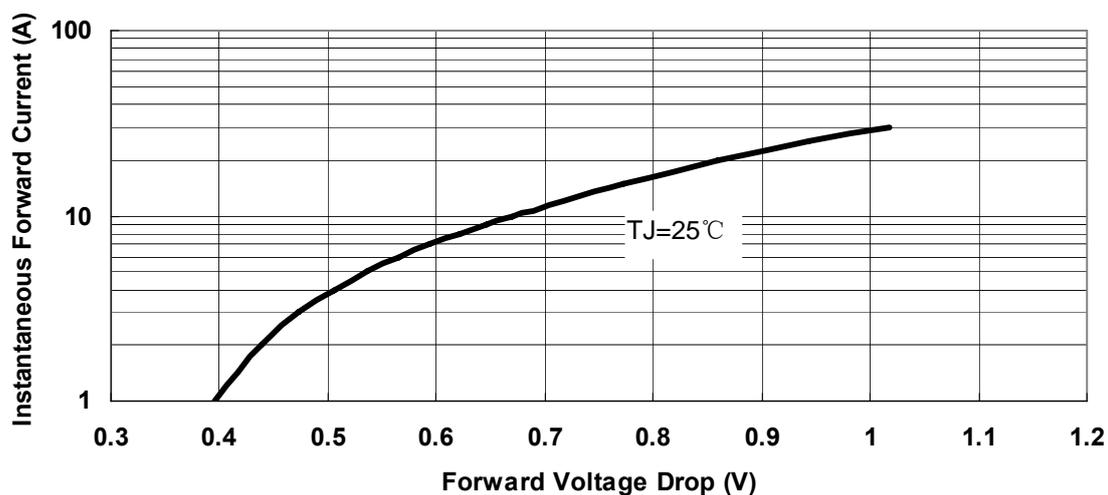


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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